

## SOT-89 Plastic-Encapsulate Transistors

### FEATURES

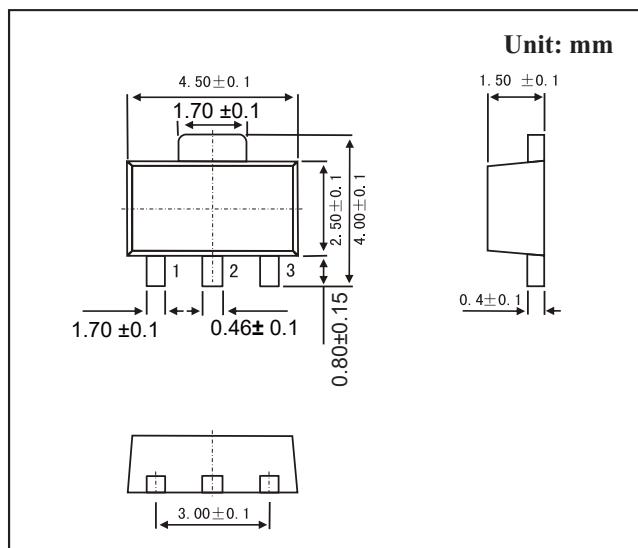
- Subminiature encapsulated flat polarized relay

### MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any

### MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)



Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-80	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current -Continuous	$I_C$	-0.4	A
Collector Power Dissipation	$P_C$	0.5	W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-80\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2\text{V}, I_C=50\text{mA}$	70		240	
	$h_{FE(2)}$	$V_{CE}=-2\text{V}, I_C=200\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-200\text{mA}, I_B=-20\text{mA}$			-0.4	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-2\text{V}, I_C=-5\text{mA}$	-0.55		-0.8	V
Transition frequency	$f_T$	$V_{CE}=-10\text{V}, I_C=-10\text{mA}$		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		14		pF

## RATINGS AND CHARACTERISTIC CURVES

